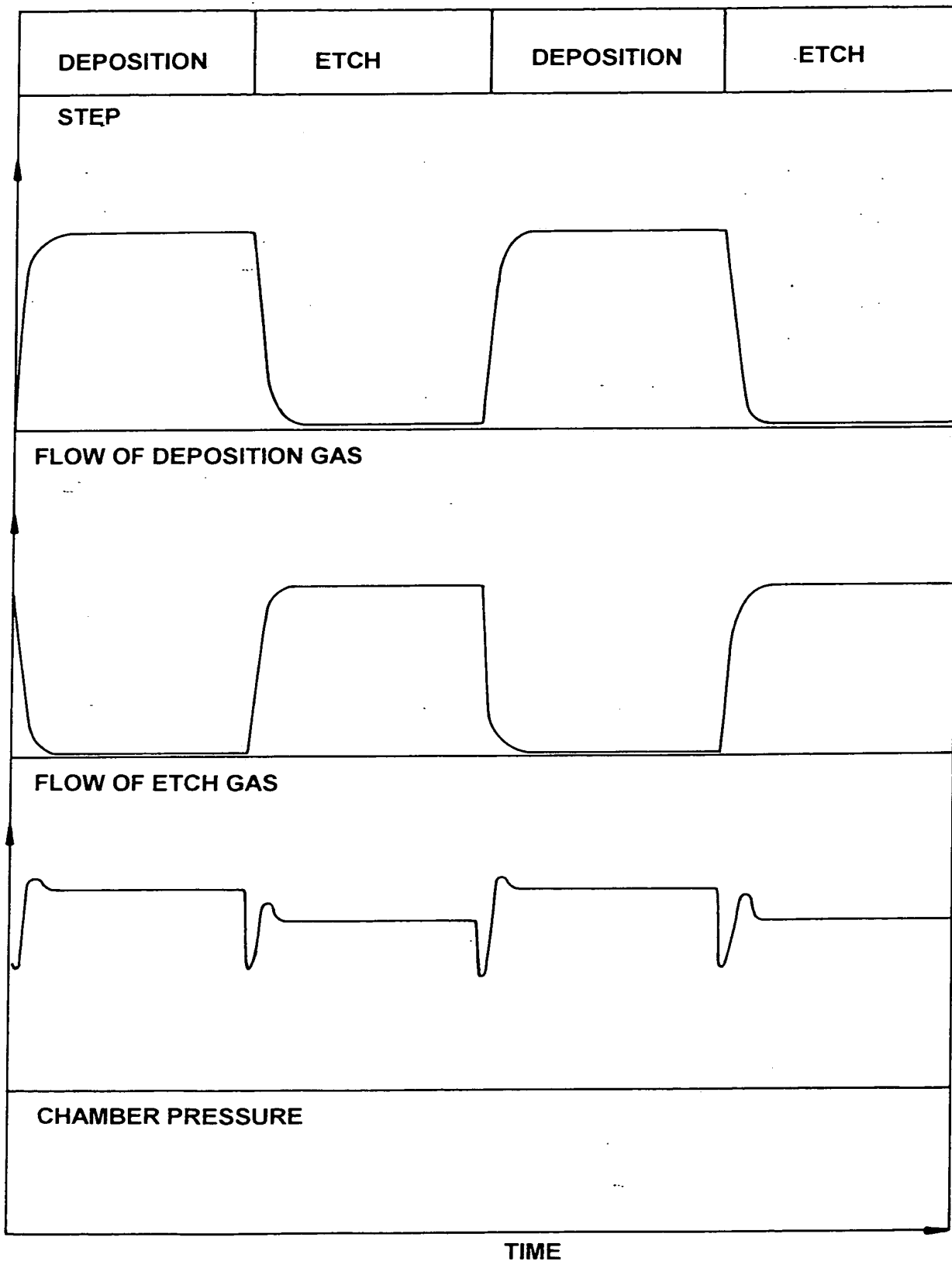


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*Fig. 1*

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DEPOSITION	ETCH	DEPOSITION	ETCH
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STEP

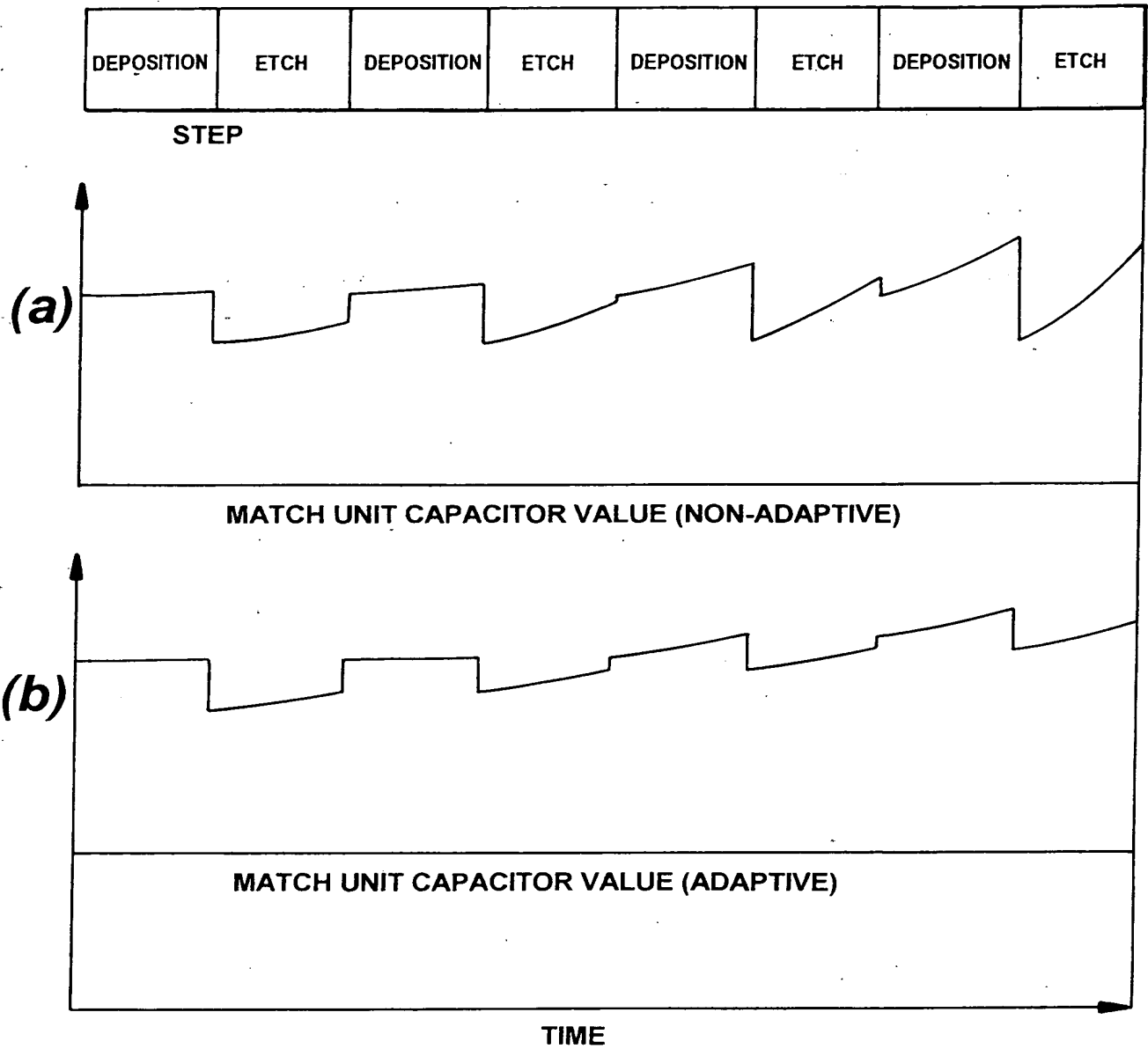
DRIVE MATCHING UNIT CAPACITORS TO PRE-DETERMINED VALUES FOR DEPOSITION	<u>AUTO MATCH ENABLED</u>	DRIVE MATCHING UNIT CAPACITORS TO PRE-DETERMINED VALUES FOR ETCH	<u>AUTO MATCH ENABLED</u>	DRIVE MATCHING UNIT CAPACITORS TO PRE-DETERMINED VALUES FOR DEPOSITION	<u>AUTO MATCH ENABLED</u>	DRIVE MATCHING UNIT CAPACITORS TO PRE-DETERMINED VALUES FOR ETCH	<u>AUTO MATCH ENABLED</u>
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MATCHING UNIT STATUS

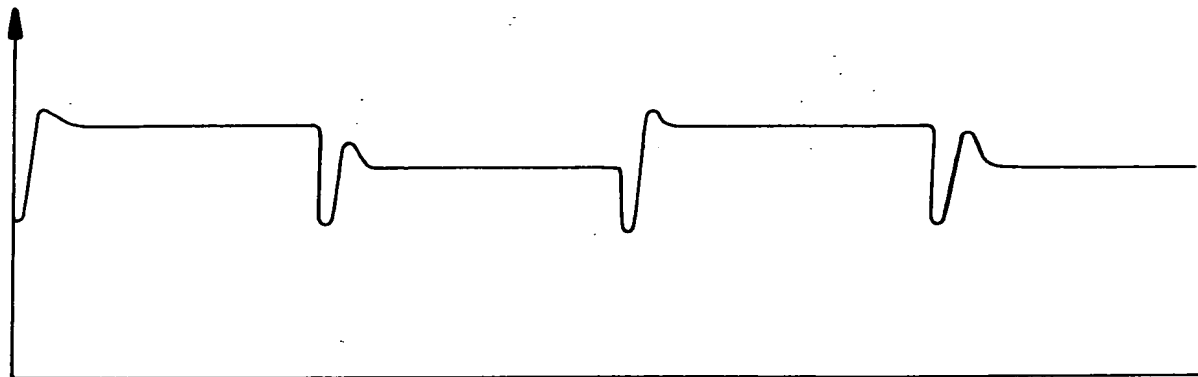
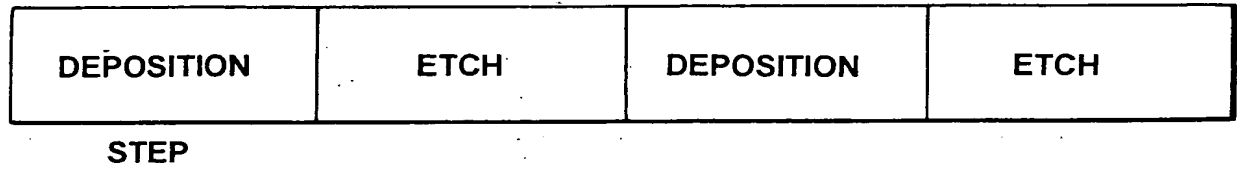
TIME

Fig. 2

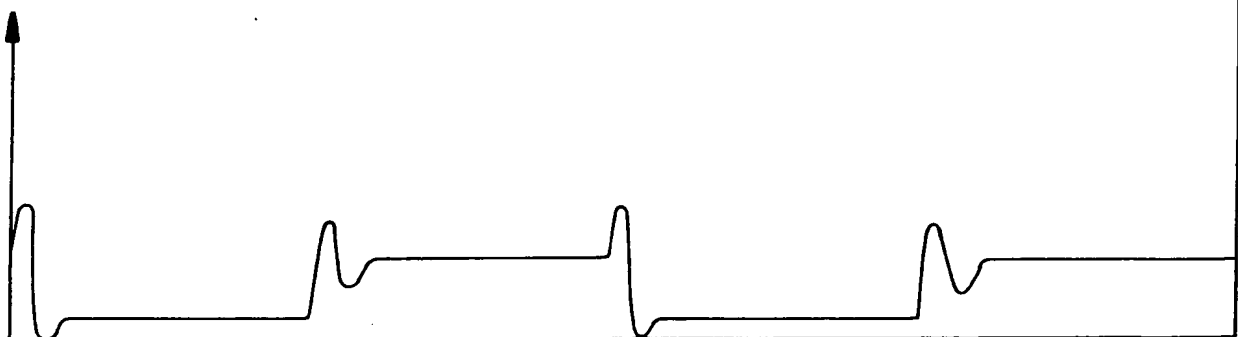
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*Fig. 3*

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(a) CHAMBER PRESSURE



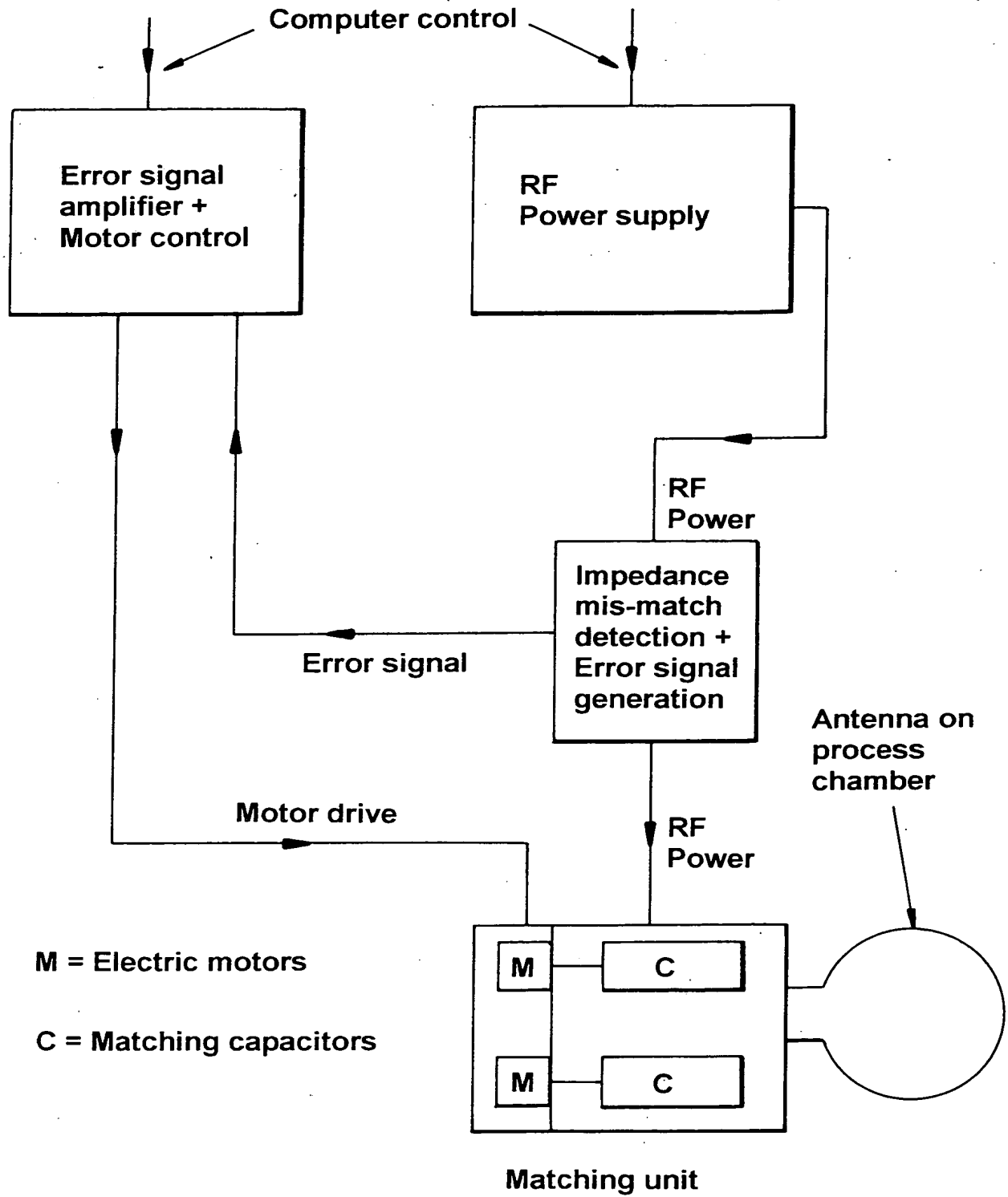
(b) FLOW OF BUFFER GAS

TIME

Fig. 4

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*Fig. 5*

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RF power fed
to circuit via
co-axial
cable and
connector,
impedance
typically
 50Ω

Capacitor to primarily
match imaginary part
of impedance

Dielectric
section of
process
chamber

Capacitor to primarily
match real part of
impedance

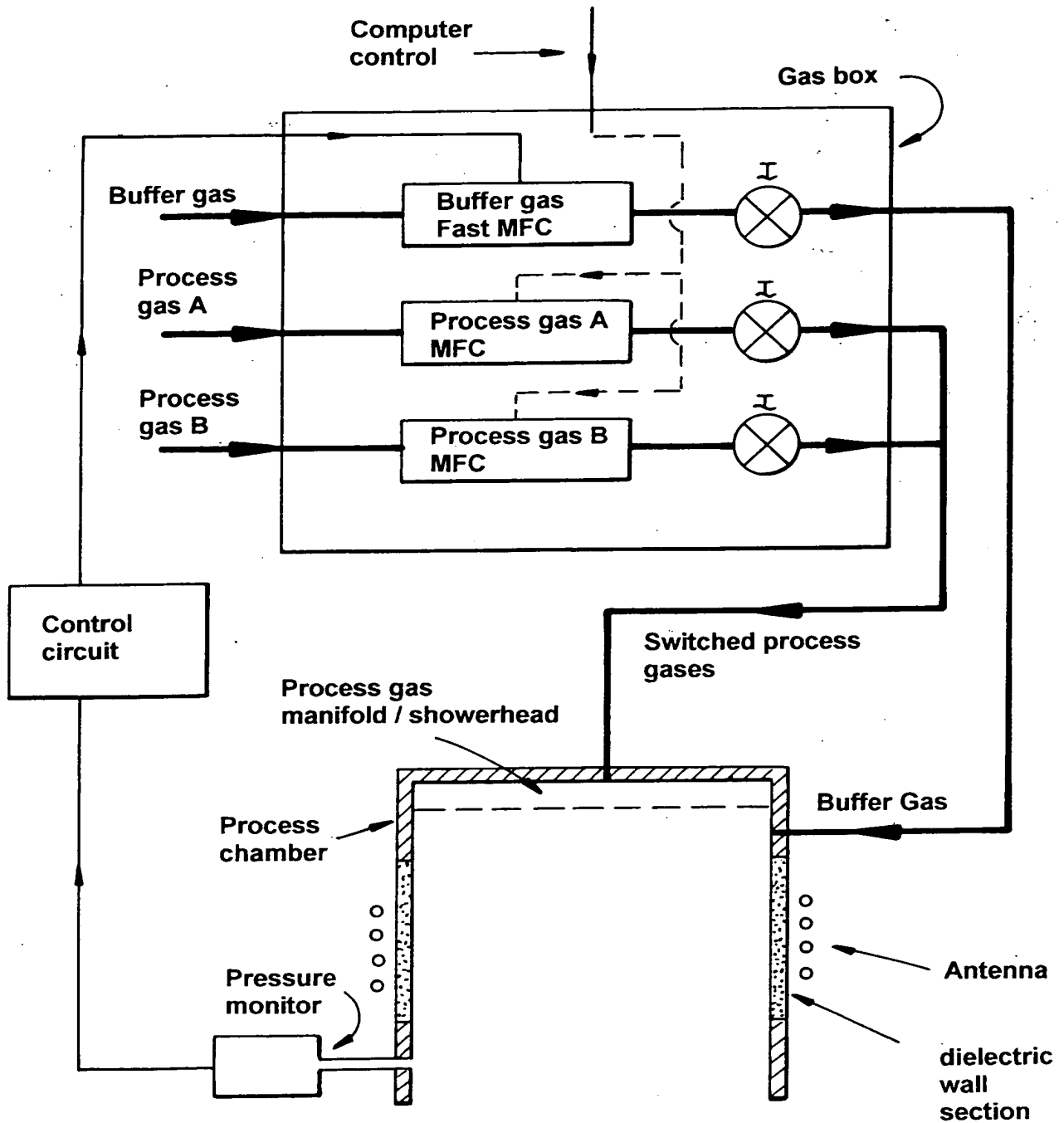
Antenna

Plasma
formed by
inductive coupling of
R.F. Power

Fig. 6

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MFC = Mass flow controller

I = Isolation valve (if required)

Fig. 7